

# MMST3906

## SOT-323 Plastic-Encapsulate Transistors

### MMST3906 TRANSISTOR (PNP)

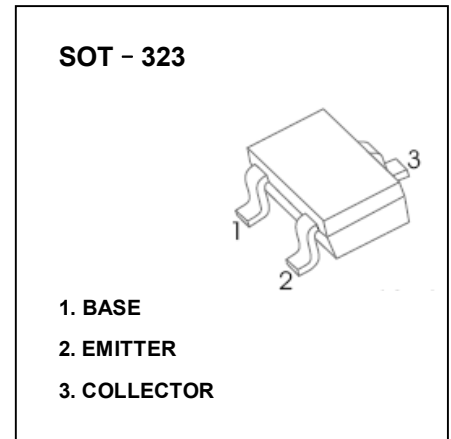
#### FEATURES

- Complementary to MMST3904

**MARKING:K5N**

#### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-40	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-200	mA
$P_C$	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^\circ\text{C/W}$
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^\circ\text{C}$

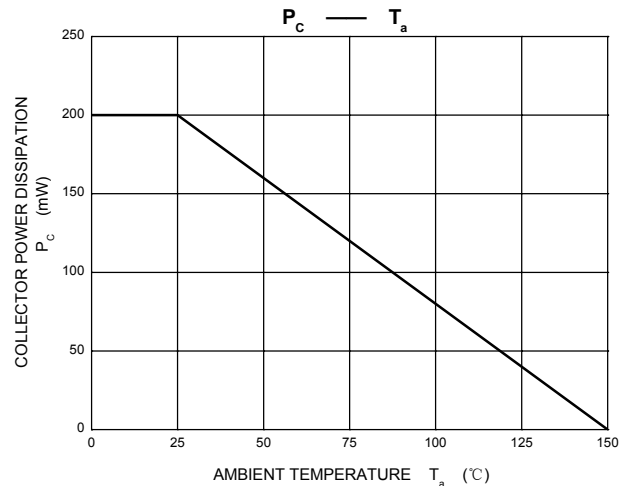
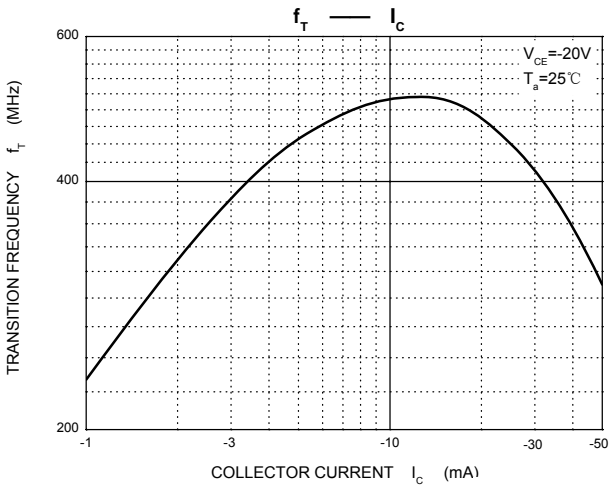
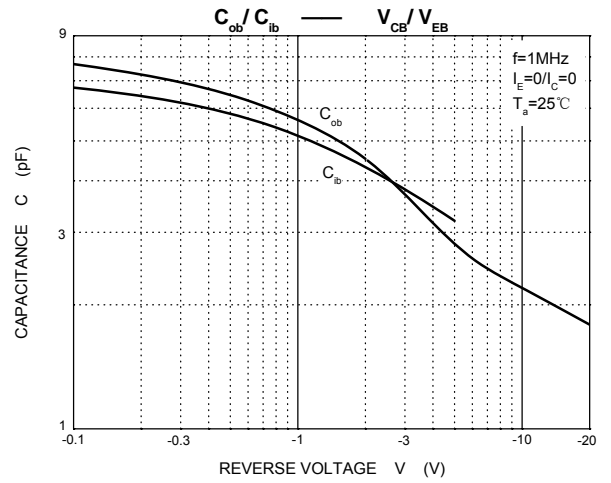
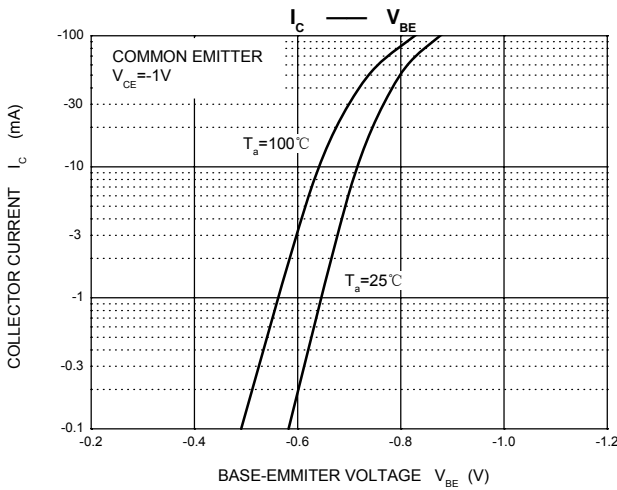
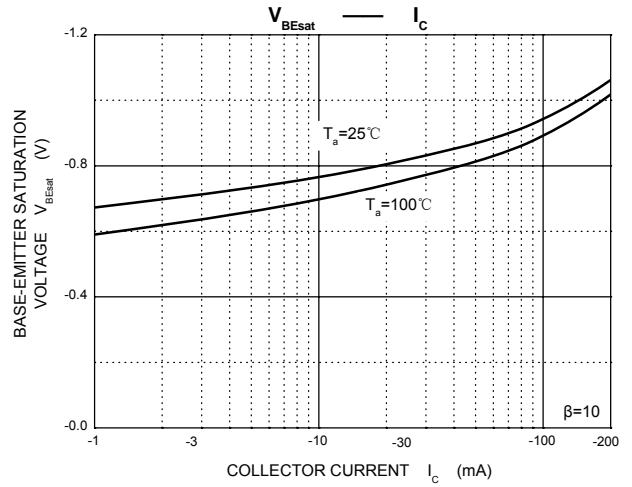
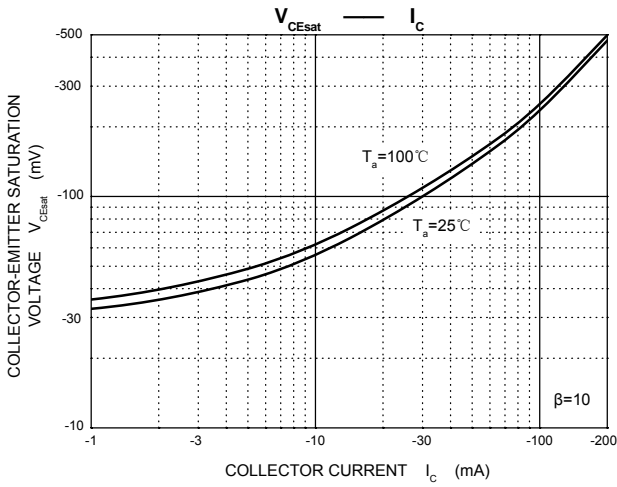
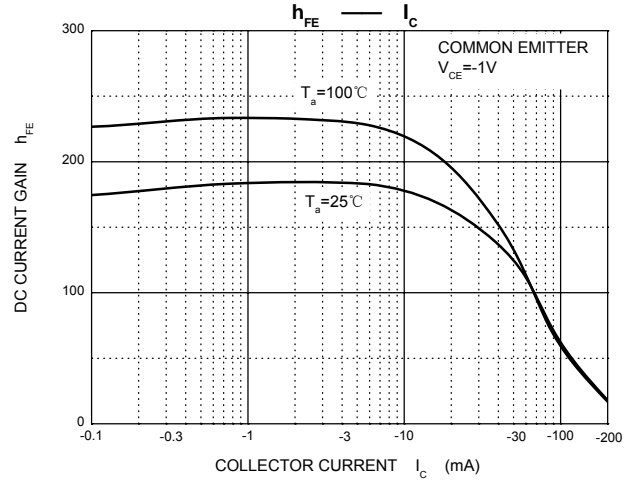
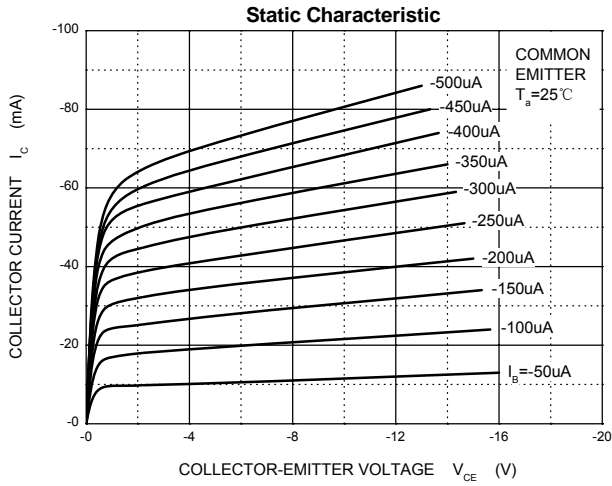


#### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}^*$	$I_C=-10\mu\text{A}, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=-1\text{mA}, I_B=0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}^*$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Base cut-off current	$I_{BL}^*$	$V_{CE}=-30\text{V}, V_{EB(off)}=-3\text{V}$			-50	nA
Collector cut-off current	$I_{CEX}^*$	$V_{CE}=-30\text{V}, V_{EB(off)}=-3\text{V}$			-50	nA
DC current gain	$h_{FE}^*$	$V_{CE}=-1\text{V}, I_C=-100\mu\text{A}$	60			
		$V_{CE}=-1\text{V}, I_C=-1\text{mA}$	80			
		$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	100		300	
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.2	V
		$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}^*$	$I_C=-10\text{mA}, I_B=-1\text{mA}$	-0.65		-0.85	V
		$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.95	V
Transition frequency	$f_T$	$V_{CE}=-20\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	250			MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-5\text{V}, I_E=0, f=1\text{MHz}$			4.5	pF
Collector output capacitance	$C_{ib}$	$V_{EB}=-0.5\text{V}, I_E=0, f=1\text{MHz}$			10	pF
Delay time	$t_d$	$V_{CC}=-3\text{V}, V_{BE(off)}=-0.5\text{V}, I_C=-10\text{mA}$			35	ns
Rise time	$t_r$	$I_{B1}=-1\text{mA}$			35	ns
Storage time	$t_s$	$V_{CC}=3\text{V}, I_C=-10\text{mA}, I_{B1}=I_{B2}=-1\text{mA}$			225	ns
Fall time	$t_f$				75	ns

\*Pulse test: pulse width  $\leq 300\mu\text{s}$ , duty cycles  $\leq 2.0\%$ .

# Typical Characteristics

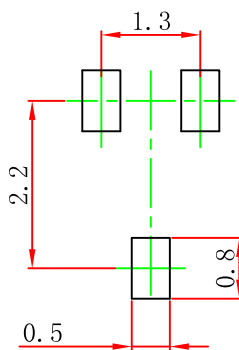


## SOT-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°		8°	

## SOT-323 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$  mm.
3. The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

[>>YONGYUTAI\(永裕泰\)](#)